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<td>Rev 1.0</td>
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Power switch only low-active support.

Iout = 1.5A

Over Current: OCB = 0
Reserved for VL812 rev B2 to simplify layout of DC12FB pin.

The pin of G1 is exposed pad land pattern and it must connect to GND.

Reserved to prevent 5V input have over shoot over 5.5V for protect ST12 DC2DC.
Power switch only low-active support.
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Reserved for VL812 rev B2 to simplify layout of DC12FB pin.

The pin of G1 is exposed pad land pattern and it must connect to GND.

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Power switch only low-active support.
25MHz +/- 30ppm Crystal

Reset Circuit

Optional for USB-IF test

93C56A or 93C66A EEPROM

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25MHz +/- 30ppm Crystal

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25MHz +/- 30ppm Crystal

Reset Circuit

Optional for USB-IF test

93C56A or 93C66A EEPROM

Optional for USB-IF test
Max Load: VDDH 350mA (continue)

\[ V_o = 0.6 \times (R_1 + R_2) / R_1 = 1.1 \text{V} \]